



Amendments to the Specification

On page 1, line 3, please delete the title and insert the following new title:

CURRENT SENSING IC WITH RESISTIVE SENSING

On page 1, line 5, insert the heading:

FIELD OF THE INVENTION

On page 1, line 26, insert the heading:

BACKGROUND OF THE INVENTION

On page 3, line 17, insert the heading:

SUMMARY OF THE INVENTION

On page 9, line 2, insert the heading:

BRIEF DESCRIPTION OF THE DRAWINGS

On page 9, line 16, insert the heading:

DETAILED DESCRIPTION OF THE INVENTION

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On page 22, line 4, please delete the title and insert the following new title:

CURRENT SENSING IC WITH RESISTIVE SENSING

On page 22, please delete the ABSTRACT and insert the following new ABSTRACT:

A power MOSFET has a main current carrying section and a sense current carrying section, with separate source electrodes. The source electrode of the main section is connected to the device source terminal. The source electrode of the sense section is connected through a current sensing resistance to the same terminal. Both sections have separate gate electrodes. By comparing a reference voltage with the sense voltage across the sensing resistance, a first control signal is provided for the gate electrode of the sense section. A control circuit includes an adjustment circuit coupled to the first control signal and to the sense voltage and provides a second control signal to the gate electrode of the main section. This second control signal maintains the gate-source voltage of the main section equal to the gate source voltage of the sense section.

On page 22, please delete the paragraph starting on line 24.